

isc Silicon PNP Power Transistor

2SB1162

DESCRIPTION

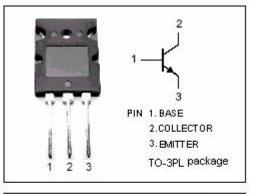
- Collector-Emitter Breakdown Voltage-: V_{(BR)CEO}= -160V(Min)
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SD1717
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

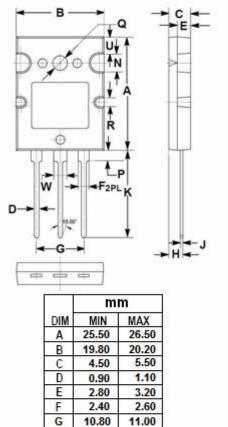
APPLICATIONS

Designed for high power amplifier applications

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|--------|------|--|
| V _{CBO} | Collector-Base Voltage -160 | | V | |
| V _{CEO} | Collector-Emitter Voltage | -160 | V | |
| V _{EBO} | Emitter-Base Voltage | -5 | V | |
| lc | Collector Current-Continuous | -12 | А | |
| I _{CP} | Collector Current-Pulse -: | | Α | |
| Pc | Collector Power Dissipation @ Tc=25℃ | 120 | W | |
| | Collector Power Dissipation @ $T_a=25^{\circ}C$ | 3.5 | | |
| TJ | Junction Temperature | 150 °C | | |
| T _{stg} | T _{stg} Storage Temperature Range | | °C | |

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)





3.10

0.50

20.00

3.90

2.40

3.10

1.90

3.90

2.90

H

κ

N

Ρ

Q

R

U

W

3.30

0.70

21.00

4.50

2.60

3.50

2.60

4.10

3.25

isc website: <u>www.iscsemi.com</u>



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|----------------------|--------------------------------------|--|-----|------|------|------|
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -8A; I _B = -0.8A | | | -2.0 | V |
| V _{BE(on)} | Base -Emitter On Voltage | I _C = -8A; V _{CE} = -5V | | | -1.8 | V |
| Ісво | Collector Cutoff Current | V _{CB} = -160V; I _E = 0 | | | -50 | μA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -3V; I _C = 0 | | | -50 | μA |
| h _{FE-1} | DC Current Gain | I _C = -20mA; V _{CE} = -5V | 20 | | | |
| h _{FE-2} | DC Current Gain | I _C = -1A; V _{CE} = -5V | 60 | | 200 | |
| h _{FE-3} | DC Current Gain | I _C = -8A; V _{CE} = -5V | 20 | | | |
| Сов | Output Capacitance | I _E = 0; V _{CB} = -10V; f _{test} = 1.0MHz | | 210 | | pF |
| f _T | Current-Gain—Bandwidth Product | I _C = -0.5A; V _{CE} = -5V | | 20 | | MHz |

h_{FE-2} Classifications

| Q | S | Р |
|--------|--------|---------|
| 60-120 | 80-160 | 100-200 |

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